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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



Marking code: Q050

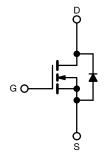
PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0065			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0045			
I _D (A) ^e	86			
Configuration	Single			

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- · Wettable flank terminals
- Low thermal resistance with 0.75 mm profile
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



AUTOMOTIVE



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK® 1212-8SLW
Lead (Pb)-free and halogen-free	SQS142ELNW (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	40	.,,	
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current e	T _C = 25 °C		86		
	T _C = 125 °C	I _D	63		
Continuous source current (diode conduction) e		I _S	64	А	
Pulsed drain current ^{a, e}		I _{DM}	271		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	22.5		
Single pulse avalanche energy	L = U. I IIIH	E _{AS}	25.3	mJ	
Maximum power dissipation ^a	T _C = 25 °C	P _D	70	- w	
	T _C = 125 °C		23		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^c			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	R_{thJA}	54	°C/W	
Junction-to-case (drain) ^d		R_{thJC}	2.1		

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. As per on JESD51-14
- e. Values based on RthJC and TC 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



Vishay Siliconix

SPECIFICATIONS (T _C = 25 °C, u	SYMBOL		T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	STIVIDOL	123	TOONDITIONS	IVIIIV.	111.	WAX.	ONIT
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		40	_	_	
Gate-source threshold voltage	V _{GS(th)}	$V_{GS} = V_{GS}, I_D = 250 \mu\text{A}$ $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		1.2	1.7	2.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = V_{GS}, I_D = 250 \text{ µA}$ $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
date source reality	'GSS	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ $V_{GS} = 0 \text{ V}$ $V_{DS} = 40 \text{ V}$			_	1	107
Zero gate voltage drain current	I _{DSS}				_	50	μΑ
2010 gate voltage aram carrent	יטפט	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, T_{J} = 175 \text{ °C}$	_	_	150	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 0.0$	$V_{DS} = 10 \text{ V}, 13 = 170 \text{ C}$ $V_{DS} \ge 5 \text{ V}$	20	_	-	Α
0.1. 0.1 0.1	·D(OII)	$V_{GS} = 4.5 \text{ V}$	103 = 0 1		0.0050	0.0065	
		V _{GS} = 10 V	I _D = 10 A	_	0.0034	0.0045	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	_	-	0.0078	Ω
		V _{GS} = 10 V		_	-	0.0095	
Forward transconductance b	9 _{fs}		= 15 V, I _D = 10 A	_	70	-	S
Dynamic ^b	0.0		, 5				
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	_	1744	2442	pF
Output capacitance	C _{oss}			-	442	619	
Reverse transfer capacitance	C _{rss}			_	39	55	
Total gate charge c	Q_g		V _{DS} = 20 V, I _D = 3 A	-	32	48	nC
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V		-	6	-	
Gate-drain charge ^c	Q _{gd}			-	6	-	
Gate resistance	R_g	f = 1 MHz		0.7	1.4	2.1	Ω
Turn-on delay time ^c	t _{d(on)}			-	11	17	
Rise time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_L = 6.67 \Omega$ $I_D \cong 3 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	4	8	ns
Turn-off delay time ^c	t _{d(off)}			-	25	38	
Fall time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Charac	teristic ^b						
Pulsed current ^a	I _{SM}			-	-	271	Α
Forward voltage	V_{SD}	I _F = 10 A, V _{GS} = 0 V		-	0.82	1.1	V
Body diode reverse recovery time	t _{rr}	$V_{DD}=32$ V, $I_{FM}=3$ A, di/dt = 100 A/μs, R = 10 Ω , L = 0.3 mH, pulse width = 2 μs		-	27	54	ns
Body diode reverse recovery charge	Q _{rr}			-	19	38	nC
Reverse recovery fall time	t _a			-	14	-	
Reverse recovery rise time	t _b			-	14	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.2	-	Α

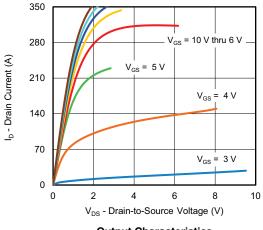
Notes

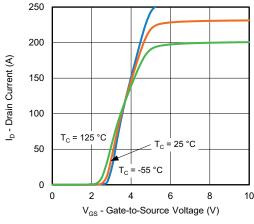
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



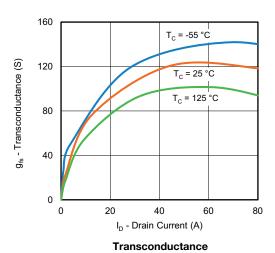
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

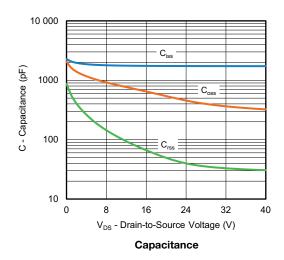


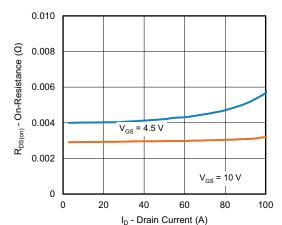


Output Characteristics

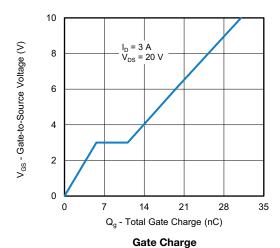






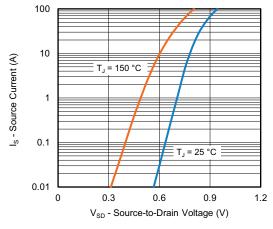


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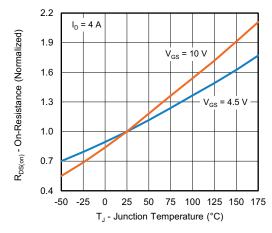




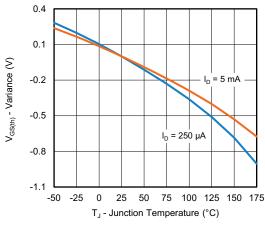
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



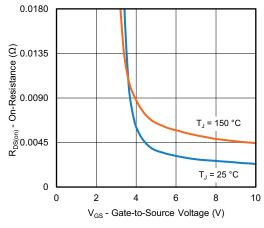
Source Drain Diode Forward Voltage



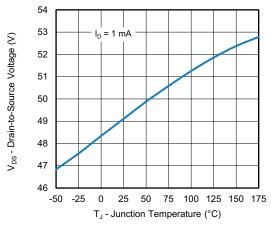
On-Resistance vs. Junction Temperature



Threshold Voltage



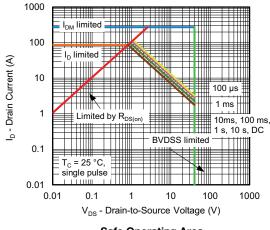
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



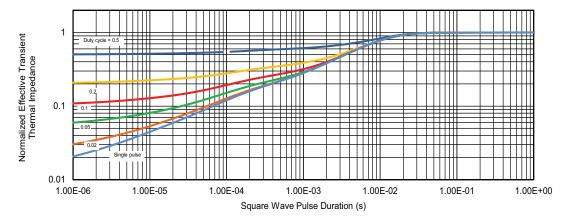
Safe Operating Area

Note

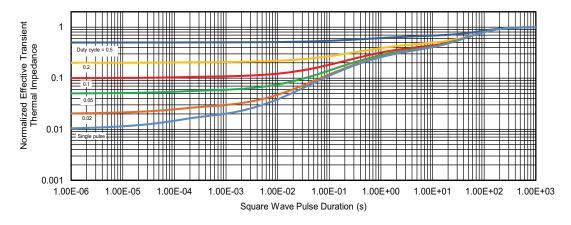
a. $V_{GS} > \mbox{minimum} \ V_{GS}$ at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

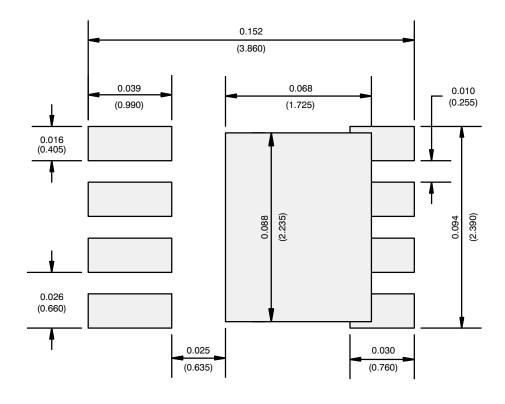
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63170.



RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1_T0_00201 PJMF380N65E1_T0_00201
PJMF280N60E1 T0 00201 PJMF600N65E1 T0 00201 PJMF900N65E1 T0 00201